CMLDM8005

SURFACE MOUNT
DUAL P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFETS

PICOmini™

SOT-563 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM8005 consists of Dual P-Channel Enhancement-mode silicon MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer Very Low $r_{DS(ON)}$ and Low Threshold Voltage.

MARKING CODE: CC8

FEATURES:

- ESD Protection up to 2kV
- 350mW Power Dissipation
- Very Low $r_{DS(ON)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, SOT-563 Surface Mount Package
- Complementary Dual N-Channel Device: CMLDM7005

APPLICATIONS:

- Load Switch / Level Shifting
- Battery Charging
- Boost Switch
- Electro-luminescent Backlighting

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	8.0	V
Continuous Drain Current (Steady State - Note 1)	I_D	650	mA
Continuous Source Current (Body Diode)	I_S	250	mA
Maximum Pulsed Drain Current	I_{DM}	1.0	A
Power Dissipation (Note 1)	P_D	350	mW
Power Dissipation (Note 2)	P_D	300	mW
Power Dissipation (Note 2)	P_D	150	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance (Note 1)	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**TYP**	**MAX**	**UNITS**
I_{GSSF}, I_{GSSR}	V_{GS}=4.5V, V_{DS}=0			10	μA
I_{DSS}	V_{DS}=16V, V_{GS}=0			100	nA
BV_{DSS}	V_{GS}=0, I_D=250μA	20			V
$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	0.5		1.0	V
V_{SD}	V_{GS}=0, I_S=250mA			1.1	V
$r_{DS(ON)}$	V_{GS}=4.5V, I_D=350mA		0.25	0.36	Ω
$r_{DS(ON)}$	V_{GS}=2.5V, I_D=300mA		0.37	0.5	Ω
$r_{DS(ON)}$	V_{GS}=1.8V, I_D=150mA			0.8	Ω

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm^2
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm^2
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm^2

R3 (27-September 2011)

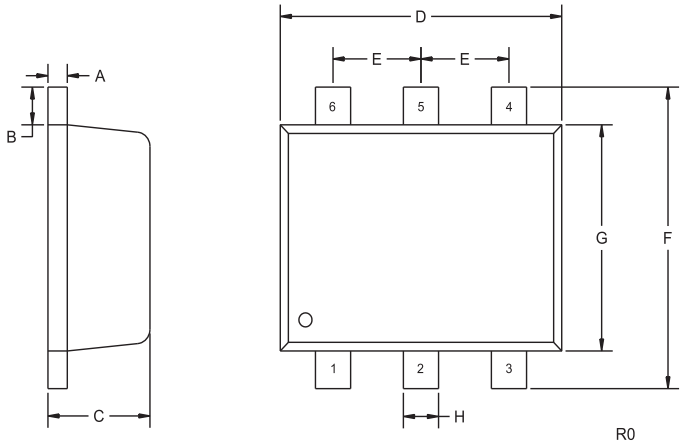
CMLDM8005

SURFACE MOUNT
DUAL P-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFETS

ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	UNITS
$Q_{g(tot)}$	V_{DS}=10V, V_{GS}=4.5V, I_D=200mA		1.2	nC
Q_{gs}	V_{DS}=10V, V_{GS}=4.5V, I_D=200mA		0.24	nC
Q_{gd}	V_{DS}=10V, V_{GS}=4.5V, I_D=200mA		0.36	nC
g_{FS}	V_{DS}=10V, I_D=200mA	0.2		S
C_{rss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		25	pF
C_{iss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		100	pF
C_{oss}	V_{DS}=16V, V_{GS}=0, f=1.0MHz		21	pF
t_{on}	V_{DD}=10V, V_{GS}=4.5V, I_D=200mA, R_G=10Ω		38	ns
t_{off}	V_{DD}=10V, V_{GS}=4.5V, I_D=200mA, R_G=10Ω		48	ns

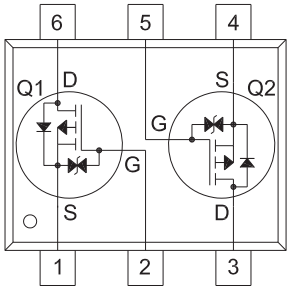
SOT-563 CASE - MECHANICAL OUTLINE



DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

PIN CONFIGURATION



LEAD CODE:
1) Source Q1
2) Gate Q1
3) Drain Q2
4) Source Q2
5) Gate Q2
6) Drain Q1

MARKING CODE: CC8

R3 (27-September 2011)